

**General Description**

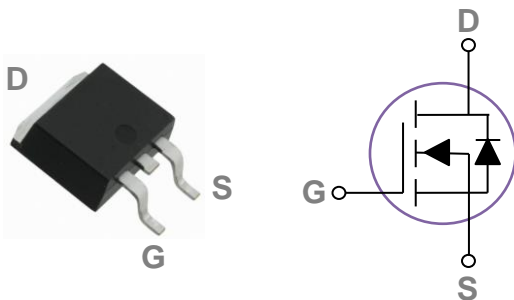
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	R <sub>DS(ON)</sub>	I <sub>D</sub>
65V	3.8mΩ	100A

**Features**

- 65V, 100A, R<sub>DS(ON)</sub> = 3.8mΩ @ V<sub>GS</sub> = 10V
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

**TO252 Pin Configuration**



**Applications**

- Networking
- Load Switch
- LED applications

**Absolute Maximum Ratings** T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	65	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current – Continuous (T <sub>C</sub> =25°C)	100	A
	Drain Current – Continuous (T <sub>C</sub> =100°C)	64	A
I <sub>DM</sub>	Drain Current – Pulsed <sup>1</sup>	400	A
EAS	Single Pulse Avalanche Energy <sup>2</sup>	273	mJ
IAS	Single Pulse Avalanche Current <sup>2</sup>	74	A
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> =25°C)	94	W
	Power Dissipation – Derate above 25°C	0.75	W/°C
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

**Thermal Characteristics**

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction to ambient	---	62	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction to Case	---	1.33	°C/W

**Electrical Characteristics ( $T_J=25\text{ }^\circ\text{C}$ , unless otherwise noted)**
**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	65	---	---	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=60V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	$\mu A$
		$V_{DS}=48V, V_{GS}=0V, T_J=85^\circ\text{C}$	---	---	10	$\mu A$
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA

**On Characteristics**

$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=30A$	---	3.2	3.8	m $\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	2	2.8	4	V
gfs	Forward Transconductance	$V_{DS}=10V, I_D=3A$	---	13	---	S

**Dynamic and switching Characteristics**

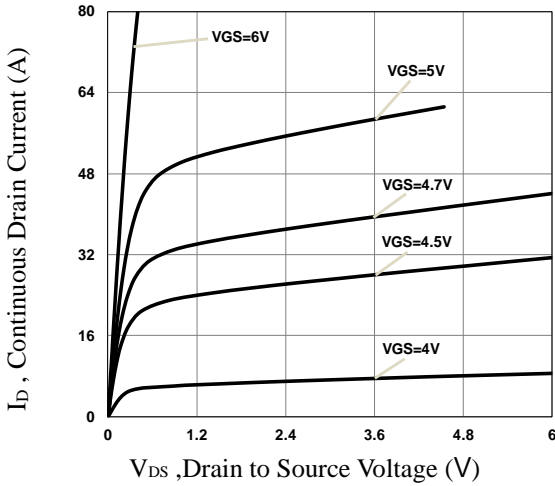
$Q_g$	Total Gate Charge <sup>3, 4</sup>	$V_{DS}=30V, V_{GS}=10V, I_D=50A$	---	49	75	nC
$Q_{gs}$	Gate-Source Charge <sup>3, 4</sup>		---	11	20	
$Q_{gd}$	Gate-Drain Charge <sup>3, 4</sup>		---	18	30	
$T_{d(on)}$	Turn-On Delay Time <sup>3, 4</sup>	$V_{DD}=30V, V_{GS}=10V, R_G=6\Omega$ $I_D=50A$	---	15	25	ns
$T_r$	Rise Time <sup>3, 4</sup>		---	22	35	
$T_{d(off)}$	Turn-Off Delay Time <sup>3, 4</sup>		---	54	80	
$T_f$	Fall Time <sup>3, 4</sup>		---	84	130	
$C_{iss}$	Input Capacitance	$V_{DS}=30V, V_{GS}=0V, F=1\text{MHz}$	---	2640	4000	pF
$C_{oss}$	Output Capacitance		---	830	1250	
$C_{rss}$	Reverse Transfer Capacitance		---	40	60	
$R_g$	Gate resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	---	1.5	---	$\Omega$

**Drain-Source Diode Characteristics and Maximum Ratings**

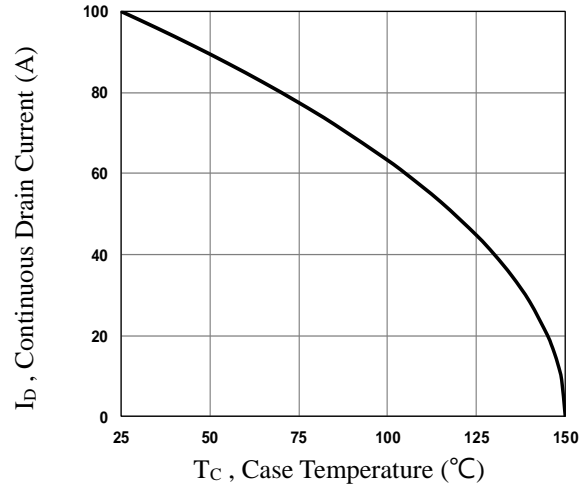
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current	$V_G=V_D=0V, \text{Force Current}$	---	---	100	A
$I_{SM}$	Pulsed Source Current		---	---	200	A
$V_{SD}$	Diode Forward Voltage	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1	V
$t_{rr}$	Reverse Recovery Time	$V_R=50V, I_S=10A$	---	70	---	ns
$Q_{rr}$	Reverse Recovery Charge	$di/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	105	---	nC

Note :

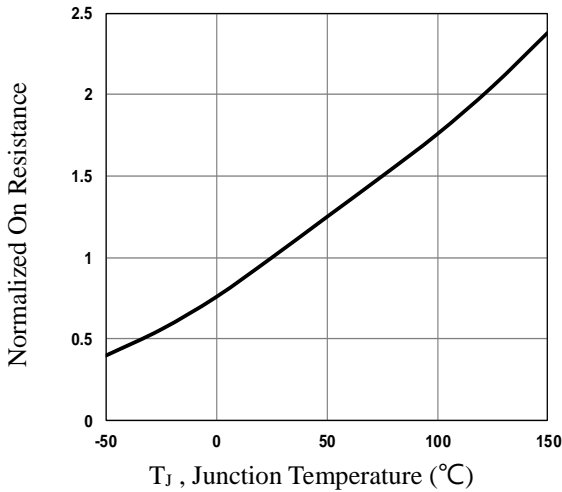
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2.  $V_{DD}=40V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=74A, R_G=25\Omega, \text{Starting } T_J=25^\circ\text{C}$ .
3. The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$ .
4. Essentially independent of operating temperature.



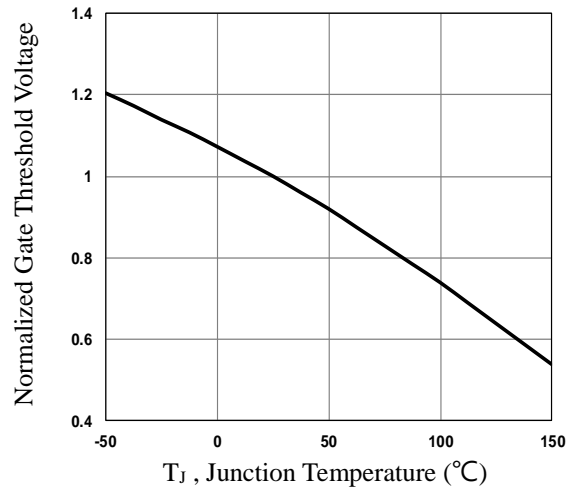
**Fig.1 Typical Output Characteristics**



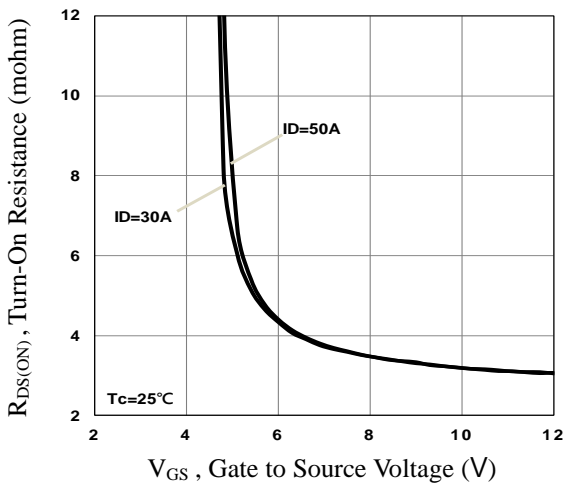
**Fig.2 Continuous Drain Current vs. T<sub>c</sub>**



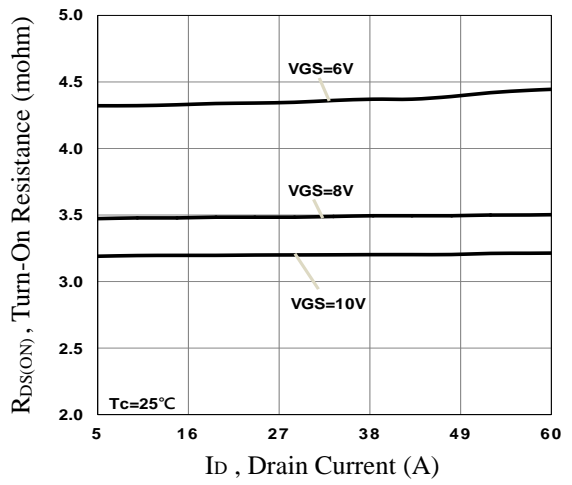
**Fig.3 Normalized R<sub>DS(on)</sub> vs. T<sub>j</sub>**



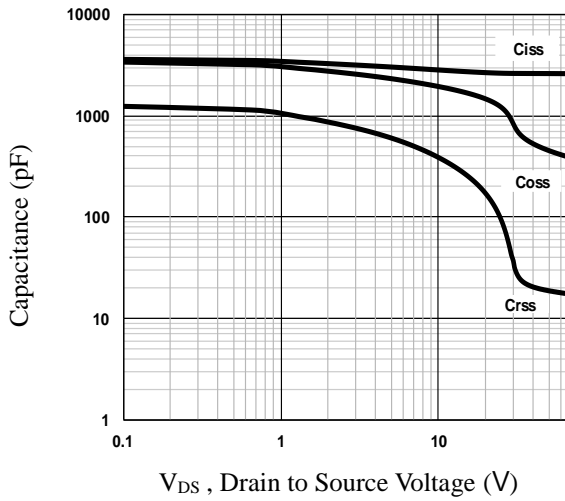
**Fig.4 Normalized V<sub>th</sub> vs. T<sub>j</sub>**



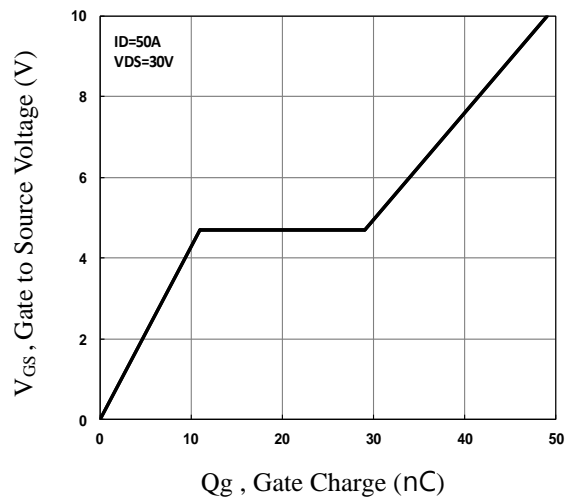
**Fig.5 Turn-On Resistance vs. V<sub>GS</sub>**



**Fig.6 Turn-On Resistance vs. I<sub>D</sub>**



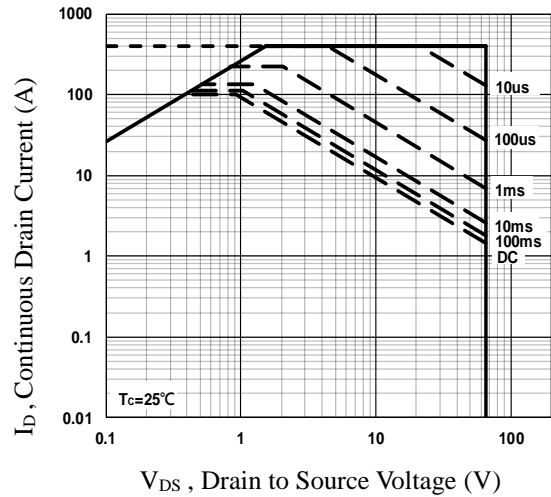
**Fig.7 Capacitance Characteristics**



**Fig.8 Gate Charge Characteristics**



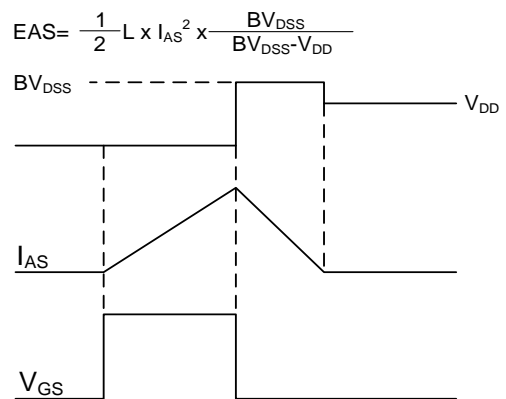
**Fig.9 Normalized Transient Impedance**



**Fig.10 Maximum Safe Operation Area**

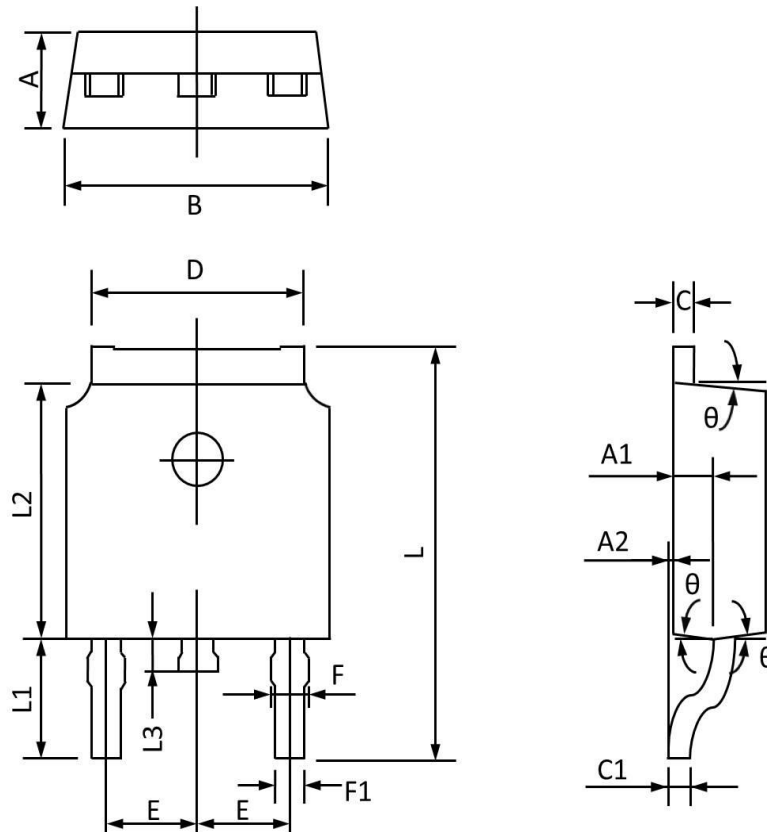


**Fig.11 Switching Time Waveform**



**Fig.12 EAS Waveform**

**TO252 PACKAGE INFORMATION**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	2.450	2.150	0.096	0.085
A1	1.200	0.910	0.047	0.036
A2	0.150	0.000	0.006	0.000
B	6.800	6.300	0.268	0.248
C	0.580	0.350	0.023	0.014
C1	0.550	0.380	0.022	0.015
D	5.500	5.100	0.217	0.201
E	2.390	2.000	0.094	0.079
F	0.940	0.600	0.037	0.024
F1	0.860	0.500	0.034	0.020
L	10.400	9.400	0.409	0.370
L1	3.000	2.400	0.118	0.094
L2	6.200	5.300	0.244	0.209
L3	1.200	0.600	0.047	0.024
θ	9°	3°	9°	3°